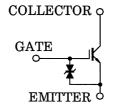
TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

GT5G103

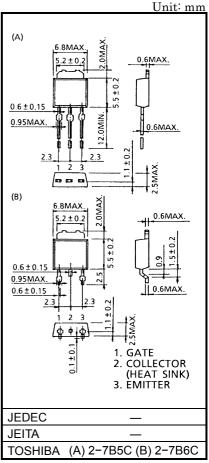
STROBE FLASH APPLICATIONS

- 3rd Generation
- High Input Impedance
- Low Saturation Voltage: VCE (sat) = 8 V (Max.) (IC = 130 A)
- Enhancement-Mode
- 4.5 V Gate Drive



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	400	V	
Gate-Emitter Voltage	DC	V _{GES}	±6	V	
	Pulse	V _{GES}	±8	V	
Collector Current	DC	Ic	5	Α	
	1 ms	I _{CP}	130	Α	
Collector Power Dissipation	Ta = 25°C	PC	1.3	W	
	Tc = 25°C	PC	20	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	

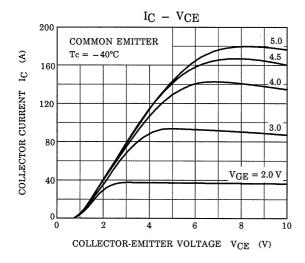


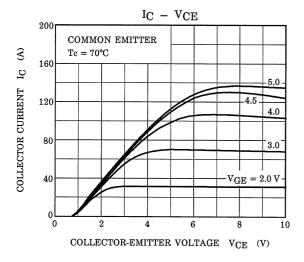
Weight: 0.36 g

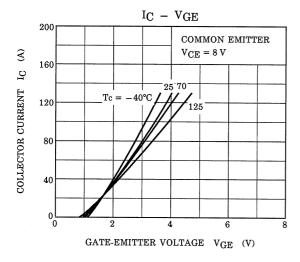
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

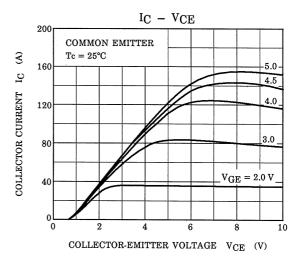
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	V _{GE} = 6 V, V _{CE} = 0	_	_	10	μΑ
Collector Cut-off C	urrent	I _{CES}	V _{CE} = 400 V, V _{GE} = 0	_	_	10	μA
Gate-Emitter Cut-o	off Voltage	V _{GE} (OFF)	I _C = 1 mA, V _{CE} = 5 V	0.5	_	1.2	V
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = 130 A, V _{GE} = 4.5 V (Pulsed)	_	5	8	V
Input Capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	1900	_	pF
Switching Time	Rise Time	t _r	$V_{IN}: t_r \leq 100 \text{ ns}$ 0 MeV 0	_	0.9	_	μs
	Turn-on Time	t _{on}		_	1.1	_	
	Fall Time	t _f		_	2.0	_	
	Turn-off Time	t _{off}		_	2.4	1	
Thermal Resistance		R _{th (j-c)}	_	_	_	6.25	°C/W

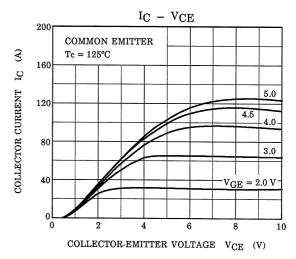
This transistor is an electrostatic sensitive device. Please handle with caution.

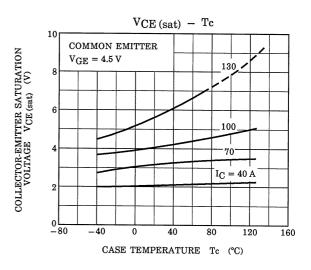


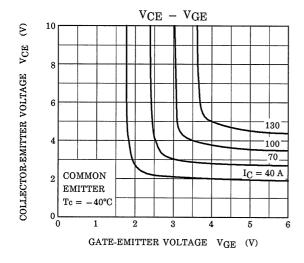


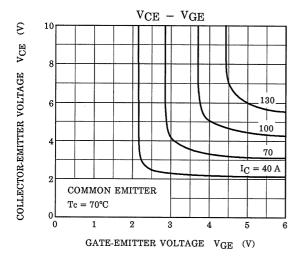


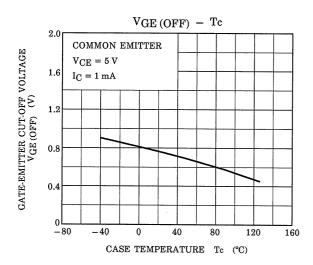


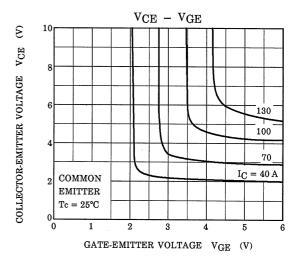


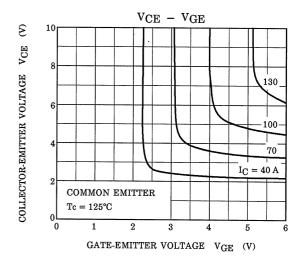


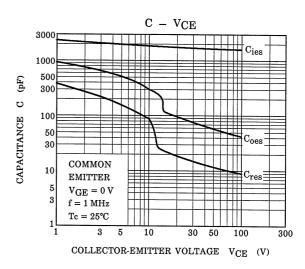






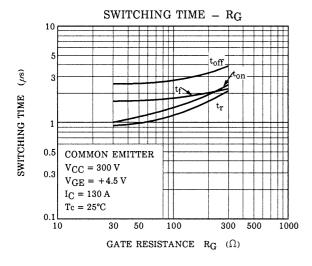


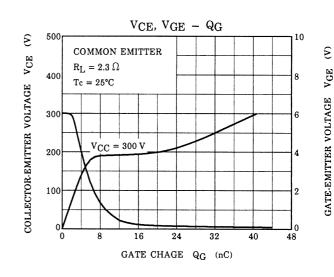


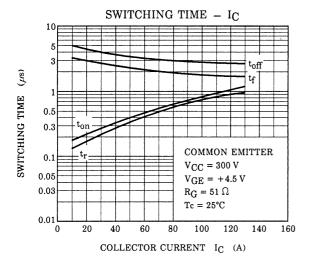


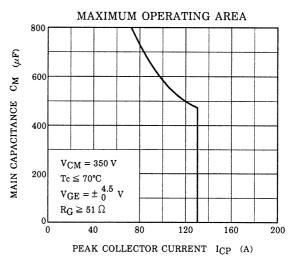
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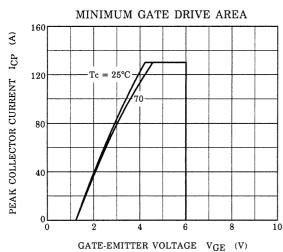
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